

CY54/74FCT157T

SCCS014 - May 1994 - Revised February 2000

Quad 2-Input Multiplexer

Features

- · Function, pinout, and drive compatible with FCT and
- FCT-C speed at 4.3 ns max. (Com'l), FCT-A speed at 5.0 ns max. (Com'l)
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- · Power-off disable feature
- · Matched rise and fall times
- · Fully compatible with TTL input and output logic levels
- ESD > 2000V
- Extended commercial range of -40°C to +85°C

64 mA (Com'I), Sink current

32 mA (Mil) 32 mA (Com'l), Source current 12 mA (Mil)

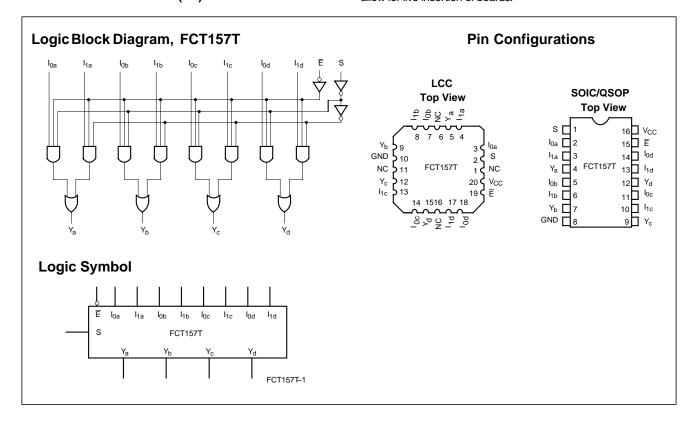
Functional Description

The FCT157T is a quad two-input multiplexer that selects four bits of data from two sources under the control of a common data Select input (S). The Enable input (\overline{E}) is Active LOW. When (E) is HIGH, all of the outputs (Y) are forced LOW regardless of all other input conditions.

Moving data from two groups of registers to four common output buses is a common use of the FCT157T. The state of the Select input determines the particular register from which the data comes. It can also be used as a function generator. The device is useful for implementing highly irregular logic by generating any four of the sixteen different functions of two variables with one variable common.

The FCT157T is a logic implementation of a four-pole, two-position switch where the position of the switch is determined by the logic levels supplied to the Select input.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.





Pin Description

| Name | Description |
|----------------|----------------------------|
| S | Common Select Input |
| Ē | Enable Inputs (Active LOW) |
| I ₀ | Data Inputs from Source 0 |
| I ₁ | Data Inputs from Source 1 |
| Υ | Non-Inverted Output |

Function Table^[1]

| | Inp | uts | | Outputs |
|---|-----|----------------|----------------|---------|
| Е | S | I ₀ | I ₁ | Y |
| Н | Х | Х | Х | L |
| L | Н | Х | L | L |
| L | Н | Х | Н | Н |
| L | L | L | Х | L |
| L | L | Н | Х | Н |

Maximum Ratings^[2,3]

(Above which the useful life may be impaired. For user guidelines, not tested.) Storage Temperature-65°C to +150°C Ambient Temperature with Power Applied-65°C to +135°C Supply Voltage to Ground Potential.....-0.5V to +7.0V DC Input Voltage-0.5V to +7.0V DC Output Voltage-0.5V to +7.0V DC Output Current (Maximum Sink Current/Pin) 120 mA Power Dissipation 0.5W Static Discharge Voltage.....>2001V (per MIL-STD-883, Method 3015)

Operating Range

| Range | Range | Ambient Temperature | v _{cc} |
|-------------------------|-------|------------------------|-----------------|
| Commercial | All | -40°C to +85°C | 5V ± 5% |
| Military ^[4] | All | −55°C to +125°C | 5V ± 10% |

Electrical Characteristics Over the Operating Range

| Parameter | Description | Test Condition | Min. | Typ. ^[5] | Max. | Unit | |
|------------------|---|---|-------|----------------------------|------|------|----|
| V _{OH} | Output HIGH Voltage | V _{CC} =Min., I _{OH} =-32 mA | Com'l | 2.0 | | | V |
| | | V _{CC} =Min., I _{OH} =-15 mA | Com'l | 2.4 | 3.3 | | V |
| | | V _{CC} =Min., I _{OH} =-12 mA | Mil | 2.4 | 3.3 | | V |
| V _{OL} | Output LOW Voltage | V _{CC} =Min., I _{OL} =64 mA | Com'l | | 0.3 | 0.55 | V |
| | | V _{CC} =Min., I _{OL} =32 mA | Mil | | 0.3 | 0.55 | V |
| V _{IH} | Input HIGH Voltage | | • | 2.0 | | | V |
| V _{IL} | Input LOW Voltage | | | | | 0.8 | V |
| V _H | Hysteresis ^[6] | All inputs | | | 0.2 | | V |
| V _{IK} | Input Clamp Diode Voltage | V _{CC} =Min., I _{IN} =-18 mA | | | -0.7 | -1.2 | V |
| II | Input HIGH Current | V _{CC} =Max., V _{IN} =V _{CC} | | | | 5 | μΑ |
| I _{IH} | Input HIGH Current | V _{CC} =Max., V _{IN} =2.7V | | | | ±1 | μΑ |
| I _{IL} | Input LOW Current | V _{CC} =Max., V _{IN} =0.5V | | | | ±1 | μΑ |
| I _{OZH} | Off State HIGH-Level Output Current | $V_{CC} = Max., V_{OUT} = 2.7V$ | | | | 10 | μА |
| I _{OZL} | Off State LOW-Level Output Current | $V_{CC} = Max., V_{OUT} = 0.5V$ | | | | -10 | μА |
| I _{OS} | Output Short Circuit Current ^[7] | V _{CC} =Max., V _{OUT} =0.0V | | -60 | -120 | -225 | mA |
| I _{OFF} | Power-Off Disable | V _{CC} =0V, V _{OUT} =4.5V | | | | ±1 | μΑ |

Note:

- H = HIGH Voltage Level. L = LOW Voltage Level. X = Don't Care
- Unless otherwise noted, these limits are over the operating free-air temperature range. Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.

- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground. T_A is the "instant on" case temperature. Typical values are at V_{CC} =5.0V, T_A =+25°C ambient. This parameter is specified but not tested. Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.



Capacitance^[6]

| Parameter | Description | Typ. ^[5] | Max. | Unit |
|------------------|--------------------|---------------------|------|------|
| C _{IN} | Input Capacitance | 5 | 10 | pF |
| C _{OUT} | Output Capacitance | 9 | 12 | pF |

Power Supply Characteristics

| Parameter | Description | Test Conditions | Typ. ^[5] | Max. | Unit |
|------------------|--|--|----------------------------|---------------------|--------|
| I _{CC} | Quiescent Power Supply Current | V _{CC} =Max., V _{IN} ≤0.2V, V _{IN} ≥V _{CC} -0.2V | 0.1 | 0.2 | mA |
| Δl _{CC} | Quiescent Power Supply Current (TTL inputs HIGH) | V _{CC} =Max., V _{IN} =3.4V, ^[8] f ₁ =0, Outputs Open | 0.5 | 2.0 | mA |
| I _{CCD} | Dynamic Power Supply Current ^[9] | V _{CC} =Max., One Input Toggling, 50% Duty Cycle, Outputs Open, OE=GND, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} −0.2V | 0.06 | 0.12 | mA/MHz |
| I _C | Total Power Supply Current ^[10] | $V_{CC}=Max., 50\%$ Duty Cycle, Outputs Open, One Input Toggling at $f_1=10$ MHz, $\overline{OE}=GND, V_{IN}\leq 0.2V$ or $V_{IN}\geq V_{CC}=0.2V$ | 0.7 | 1.4 | mA |
| | | V _{CC} =Max., 50% Duty Cycle, Outputs Open, One Input Toggling at f ₁ =10 MHz, OE=GND, V _{IN} =3.4V or V _{IN} =GND | 1.0 | 2.4 | mA |
| | | V_{CC} =Max., 50% Duty Cycle, Outputs Open, Four Bits Toggling at f_1 =2.5 MHz, \overline{OE} =GND, V_{IN} ≤0.2V or V_{IN} ≥ V_{CC} -0.2V | 0.7 | 1.4 ^[11] | mA |
| | | V _{CC} =Max., 50% Duty Cycle, Outputs Open, Four Bits Toggling at f ₁ =2.5 MHz, OE=GND, V _{IN} =3.4V or V _{IN} =GND | 1.7 | 5.4 ^[11] | mA |

Notes:

8. Per TTL driven input (V_{IN}=3.4V); all other inputs at V_{CC} or GND.

9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

10. I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}
I_C = I_{CC}+ΔI_{CC}D_HN_T+I_{CC}D(f₀/2 + f₁N₁)
I_{CC} = Quiescent Current with CMOS input levels
ΔI_{CC} = Power Supply Current for a TTL HIGH input (V_{IN}=3.4V)
D_H = Duty Cycle for TTL inputs HIGH
N_T = Number of TTL inputs at D_H
I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL)
f₀ = Clock frequency for registered devices, otherwise zero

f₀ = Clock frequency for registered devices, otherwise zero
f₁ = Input signal frequency
N₁ = Number of inputs changing at f₁
All currents are in milliamps and all frequencies are in megahertz.

11. Values for these conditions are examples of the I_{CC} formula. These limits are specified but not tested.



Switching Characteristics Over the Operating Range

| | | FCT157T | | FCT157AT | | | | FCT157CT | | | | |
|--------------------------------------|-----------------------------|----------------------|------------|----------------------|--------------------------|----------------------|-------|----------------------|------|--------|------------------------------|-----|
| | | Commo | Commercial | | Commercial Military Comm | | Commo | Commercial Com | | ercial | | Fig |
| Parameter | Description | Min. ^[12] | Max. | Min. ^[12] | Max. | Min. ^[12] | Max. | Min. ^[12] | Max. | Unit | Fig. No. ^{[13}] | |
| t _{PLH} t _{PHL} | Propagation Delay I to Y | 1.5 | 6.0 | 1.5 | 5.8 | 1.5 | 5.0 | 1.5 | 4.3 | ns | 1, 3 | |
| t _{PLH} t _{PHL} | Propagation Delay E to Y | 1.5 | 10.5 | 1.5 | 7.4 | 1.5 | 6.0 | 1.5 | 4.8 | ns | 1, 5 | |
| t _{PLH} t _{PHL} | Propagation Delay S to Y | 1.5 | 10.5 | 1.5 | 8.1 | 1.5 | 7.0 | 1.5 | 5.2 | ns | 1, 3 | |

Ordering Information

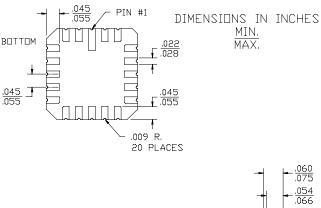
| Speed (ns) | Ordering Code | Package Name | Package Type | Operating Range |
|---------------|----------------------|-----------------|-------------------------------------|--------------------|
| 4.3 | CY74FCT157CTQCT | Q1 | 16-Lead (150-Mil) QSOP | Commercial |
| | CY74FCT157CTSOC/SOCT | S1 | 16-Lead (300-Mil) Molded SOIC | |
| 5.0 | CY74FCT157ATQCT | Q1 | 16-Lead (150-Mil) QSOP | Commercial |
| | CY74FCT157ATSOC/SOCT | S1 | 16-Lead (300-Mil) Molded SOIC | |
| 5.8 | CY54FCT157ATLMB | L61 | 20-Pin Square Leadless Chip Carrier | Military |

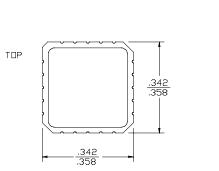
Note:

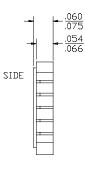
- Minimum limits are specified but not tested on Propagation Delays.
 See "Parameter Measurement Information" in the General Information Section

Document #: 38-00288-C **Package Diagrams**

20-Pin Square Leadless Chip Carrier L61 MIL-STD-1835 C-2A



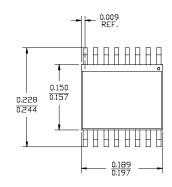


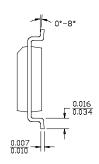


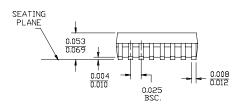


Package Diagrams (continued)

16-Lead Quarter Size Outline Q1

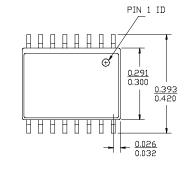




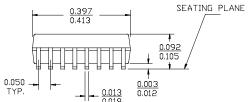


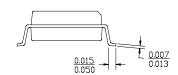
DIMENSIONS IN INCHES MIN. MAX.
LEAD COPLANARITY 0.004 MAX.

16-Lead Molded SOIC S1



DIMENSIONS IN INCHES $\frac{\text{MIN.}}{\text{MAX.}}$ LEAD COPLANARITY 0.004 MAX.





IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 2000, Texas Instruments Incorporated